

### DAP222 SWITCHING DIODE

#### FEATURES:

Power dissipation

$P_D$ : 150 mW ( $T_{amb}=25^{\circ}C$ )

Collector current

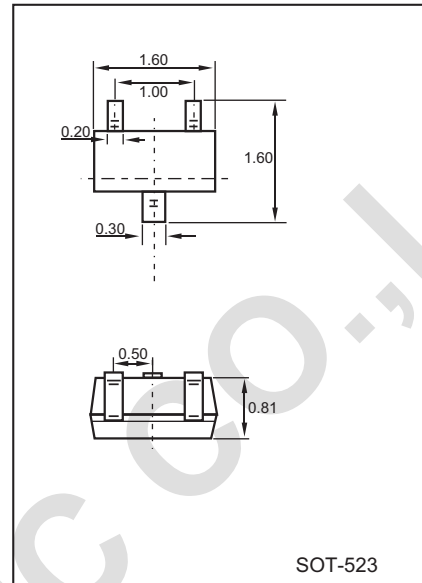
$I_F$ : 100 mA

Collector-base voltage

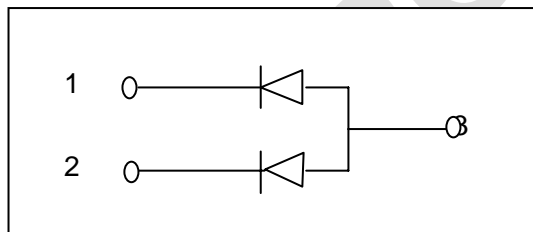
$V_R$ : 80 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### CIRCUIT:



#### MARKING: P

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	$I_R$	$V_R=70V$		0.1	$\mu A$
Forward voltage	$V_F$	$I_F=100mA$		1.2	V
Diode capacitance	$C_D$	$V_R=6V, f=1MHz$		3.5	pF
Reverse recovery time	$t_{rr}$	$V_R=6V, I_F=5mA$		4	ns